Notification about the transfer of the semiconductor business

The semiconductor business of Panasonic Corporation was transferred on September 1, 2020 to Nuvoton Technology Corporation (hereinafter referred to as "Nuvoton"). Accordingly, Panasonic Semiconductor Solutions Co., Ltd. became under the umbrella of the Nuvoton Group, with the new name of Nuvoton Technology Corporation Japan (hereinafter referred to as "NTCJ").

In accordance with this transfer, semiconductor products will be handled as NTCJ-made products after September 1, 2020. However, such products will be continuously sold through Panasonic Corporation.

Publisher of this Document is NTCJ.

If you would find description "Panasonic" or "Panasonic semiconductor solutions", please replace it with NTCJ.

* Except below description page

"Request for your special attention and precautions in using the technical information and semiconductors described in this book"

Nuvoton Technology Corporation Japan



FL6L52030L

MOS FET FL6L52030L

Silicon P-channel MOSFET(FET) Silicon epitaxial planar type(SBD)

For switching For DC-DC Converter

Features

• Low drain-source ON resistance : RDS (on) typ. = $300 \text{ m}\Omega$ (VGS = -4.0 V)

• Low drive voltage : 2.5 V drive

 Halogen-free / RoHS compliant (EU RoHS / UL-94 V-0 / MSL:Level 1 compliant)

Absolute Maximum Ratings Ta = 25 °C

項目 Drain to Source Voltage

Gate to Source Voltage

Peak drain current

Reverse voltage

Channel temperature

SBD Forward current (Average)

Junction temperature

Storage temperature

Total power dissipation

Overall Operating ambient temperature

which has more than 300mm².

Marking Symbol Y3

Packaging

FET Drain current

Embossed type (Thermo-compression sealing) 10 000 pcs / reel (standard)

Note: *1 Glass epoxy board (25.4 x 25.4 x t0.8 mm) coated with copper foil,

PD absolute maximum rating without a heat shink: 150 mW

Symbol

VDS

VGS

ID

IDp

Tch

VR

IF(AV)

Τj

PD

Topr

Tstg

Rating

-20

±12

-1.0

-4.0

150

20

800

125

540

-40 to +85

-55 to +125

Unit

V

V

A

А

°C

V

mΑ

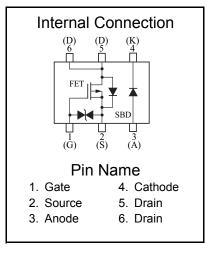
°C

mW

°C

°C

	Unit : mm				
1. Gate	4. Cathode				
2. Source	e 5. Drain				
3. Anode					
Panasonic	WSSMini6-F1				
JEITA	_				
Code					





MOS FET FL6L52030L

■ Electrical Characteristics Ta = 25 °C ± 3 °C

FET (P-ch.)

Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Drain-source surrender voltage	VDSS	ID = -1.0 mA, VGS = 0	-20			V
Drain-source cutoff current	IDSS	VDS = -20 V, VGS = 0			-1.0	μA
Gate-source cutoff current	IGSS	VGS = ±10 V, VDS = 0			±10	μA
Gate threshold voltage	VTH	ID = -1.0 mA, VDS = -10 V	-0.45	-1.0	-1.5	V
Drain-source ON resistance *1	RDS(on)	ID = -0.5 A, VGS = -4.0 V		300	420	mΩ
		ID = -0.5 A, VGS = -2.5 V		420	560	
Forward transfer admittance ^{*1}	Yfs	ID = -0.5 A, VDS = -10 V, f = 1 kHz	1.0			S
Short-circuit input capacitance (Common source)	Ciss			80		
Short-circuit output capacitance (Common source)	Coss	VDS = -10 V, VGS = 0 V, f = 1 MHz		12		pF
Reverse transfer capacitance (Common source)	Crss			12		
Turn-on delay time ^{*2}	td(on)	VDD = -15 V, VGS = 0 to - 4.0 V		12		ne
Rise time ^{*2}	tr	ID = -0.5 A		6		ns
Turn-off delay time ^{*2}	td(off)	VDD = -15 V, VGS = - 4.0 to 0 V		17		ns
Fall time ^{*2}	tf	ID = -0.5 A		10		

Note: 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 Measuring methods for transistors. 2. *1 Pulse measurement

*2 Measurement circuit for Turn-on Delay Time/Rise Time/Turn-off Delay Time/Fall Time

SBD

Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Forward voltage	VF	IF = 800 mA			0.47	V
Reverse current	IR	VR = 20 V			80	μA

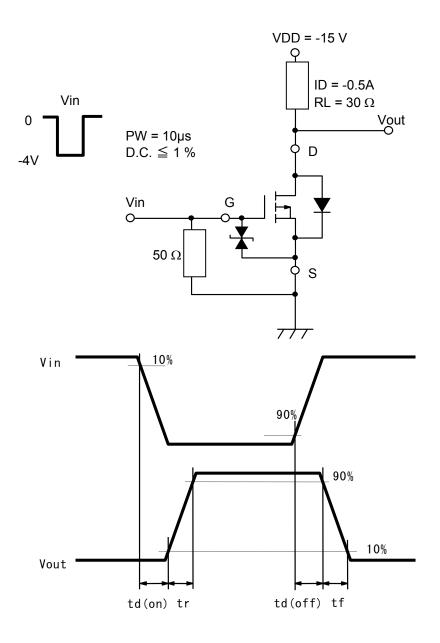
Note: Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7031 Measuring methods for diodes.

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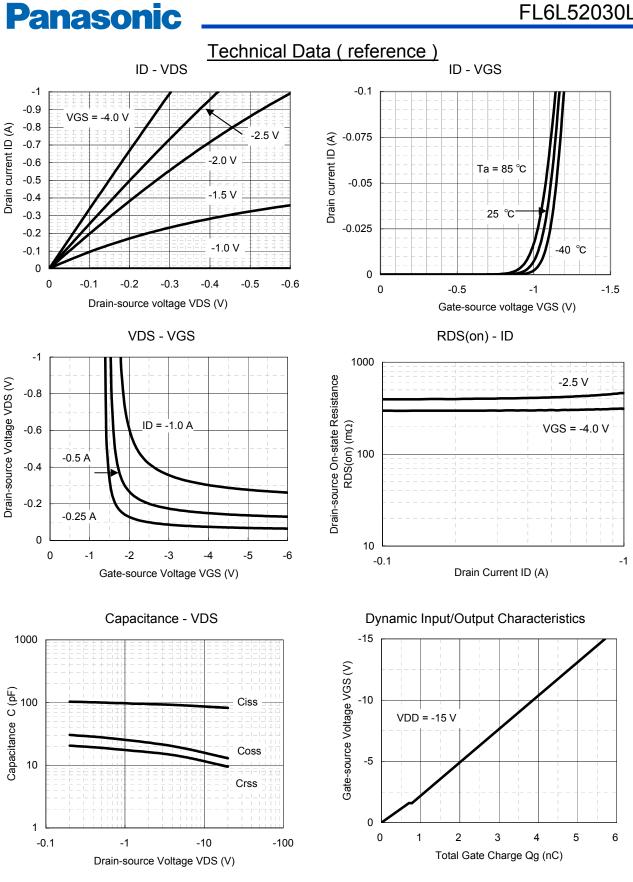
MOS FET FL6L52030L

*2 Measurement circuit for Turn-on Delay Time/Rise Time/Turn-off Delay Time/Fall Time

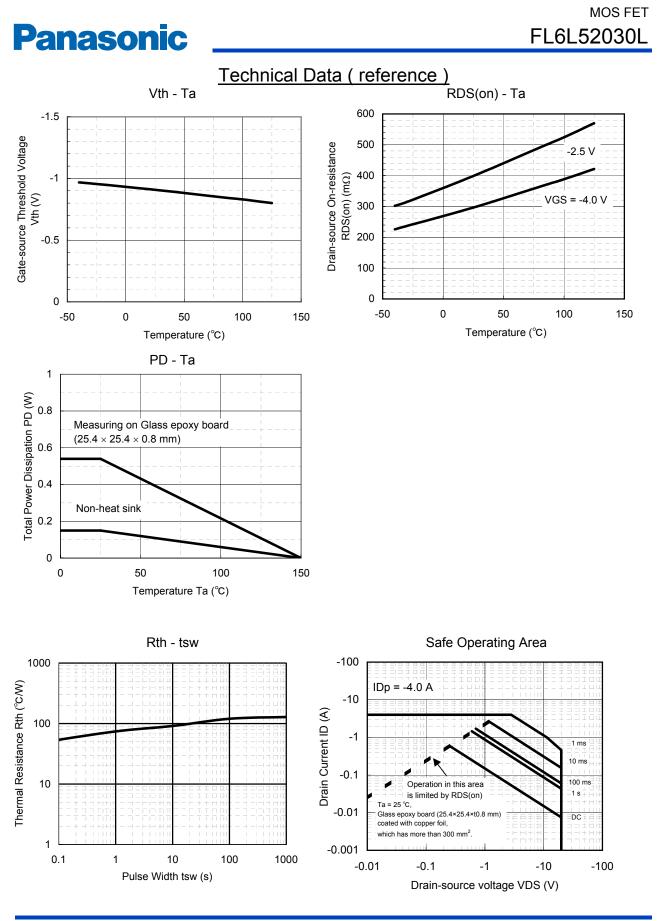


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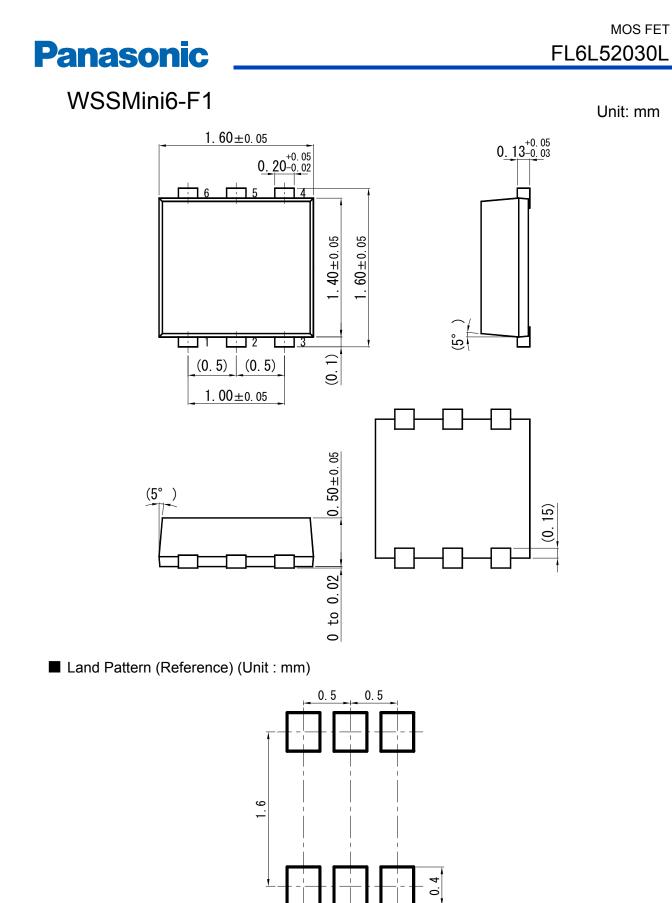
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Established : 2011-03-22 Revised : 2013-10-18

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